

## Description

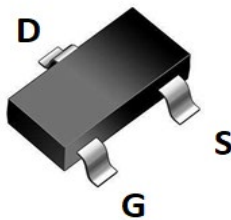
### JMT P-channel Enhancement Mode Power MosFET

#### Features

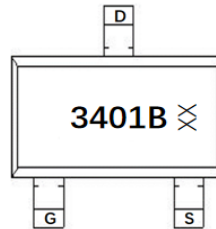
- -30V, -4A  
 $R_{DS(ON)} < 64m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 74m\Omega @ V_{GS} = -4.5V$   
 $R_{DS(ON)} < 96m\Omega @ V_{GS} = -2.5V$
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free

#### Applications

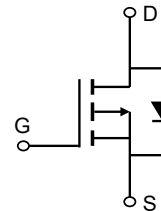
- Load Switch
- PWM Application
- Power Management



SOT-23-3L Top View



Marking and Pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
3401B	JMTJ3401B	TAPING	SOT-23-3L	7"	3000	120000

## Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
$V_{DS}$	Drain-to-Source Voltage	-30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-4
		$T_A = 100^\circ\text{C}$	-3
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	-16	A
$P_D$	Power Dissipation	$T_A = 25^\circ\text{C}$	1.1
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(2)</sup>	110	$^\circ\text{C/W}$
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$



## Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V	-30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	-	-	1.0	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.6	-0.95	-1.3	V
R <sub>DS(ON)</sub>	Static Drain-Source ON-Resistance <sup>(3)</sup>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4A	-	49	64	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A	-	57	74	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3A	-	74	96	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -15V, f = 1MHz	-	553	-	pF
C <sub>oss</sub>	Output Capacitance		-	57	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	35	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 0 to -4.5V V <sub>DS</sub> = -15V, I <sub>D</sub> = -3A	-	6.5	-	nC
Q <sub>gs</sub>	Gate Source Charge		-	1.4	-	nC
Q <sub>gd</sub>	Gate Drain ("Miller") Charge		-	1.7	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -15V I <sub>D</sub> = -3A, R <sub>GEN</sub> = 3Ω	-	10	-	ns
t <sub>r</sub>	Turn-On Rise Time		-	86	-	ns
t <sub>d(off)</sub>	Turn-Off DelayTime		-	150	-	ns
t <sub>f</sub>	Turn-Off Fall Time		-	357	-	ns
<b>Drain-Source Diode Characteristics and Max Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = -4A	-	-	-1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> = -3A, di/dt = 80A/us	-	36	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	5	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2. R<sub>θJA</sub> is measured with the device mounted on a 1inch<sup>2</sup> pad of 2oz copper FR4 PCB
  3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

## Typical Performance Characteristics

Figure 1: Output Characteristics

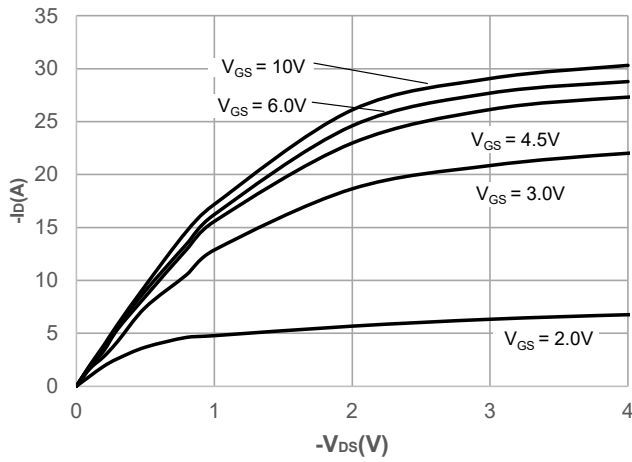


Figure 2: Typical Transfer Characteristics

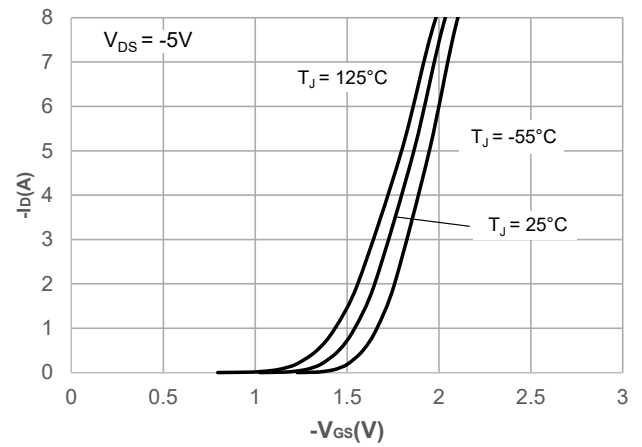


Figure 3: On-resistance vs. Drain Current

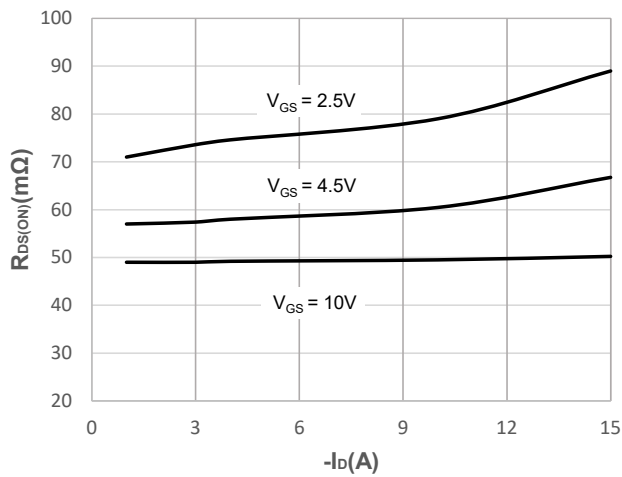


Figure 4: Body Diode Characteristics

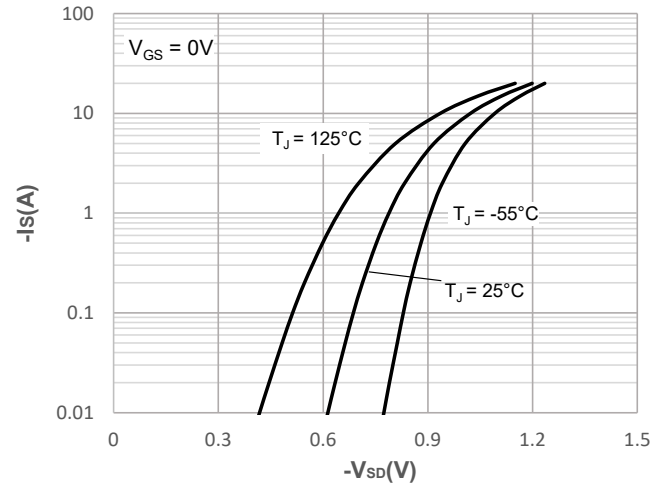


Figure 5: Gate Charge Characteristics

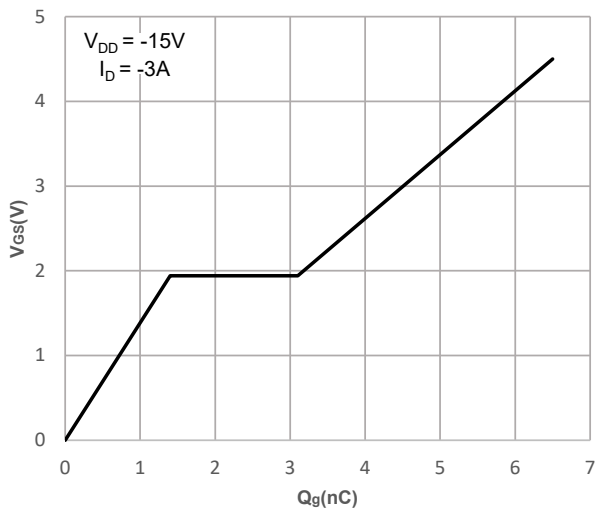
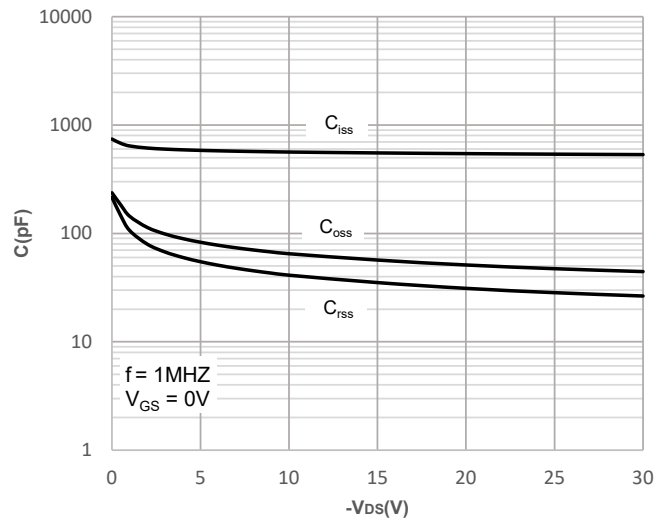


Figure 6: Capacitance Characteristics



## Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

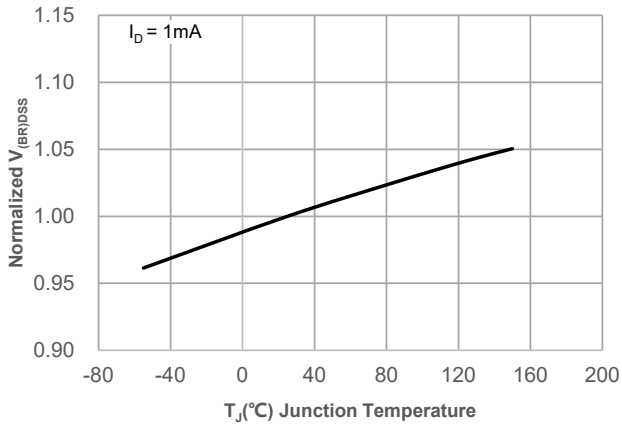


Figure 8: Normalized on Resistance vs. Junction Temperature

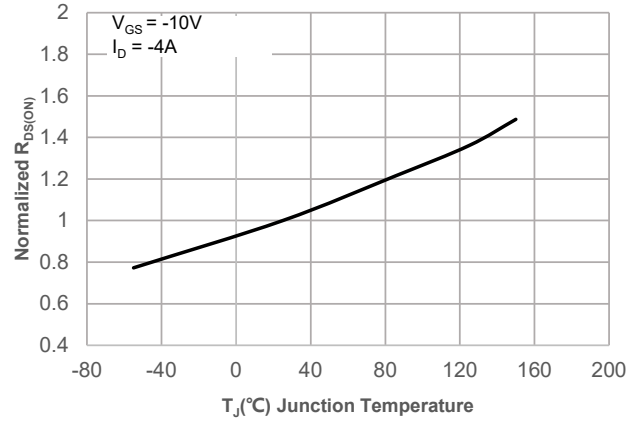


Figure 9: Maximum Safe Operating Area

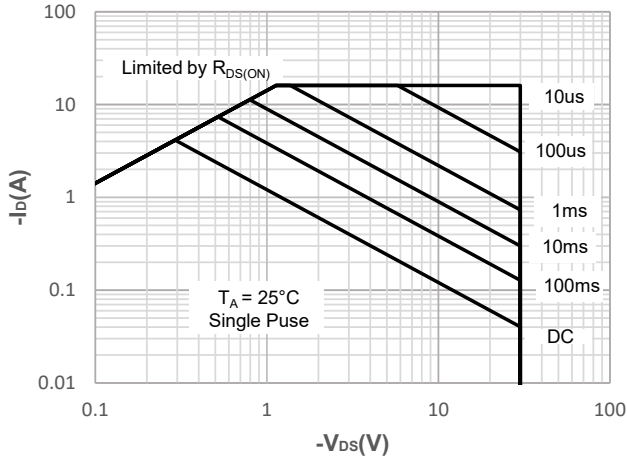


Figure 10: Maximum Continuous Drianc Current vs. Ambient Temperature

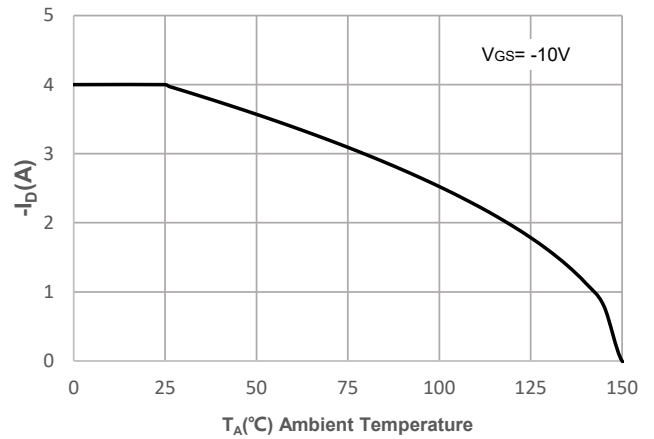


Figure 11: Normalized Maximum Transient Thermal Impedance

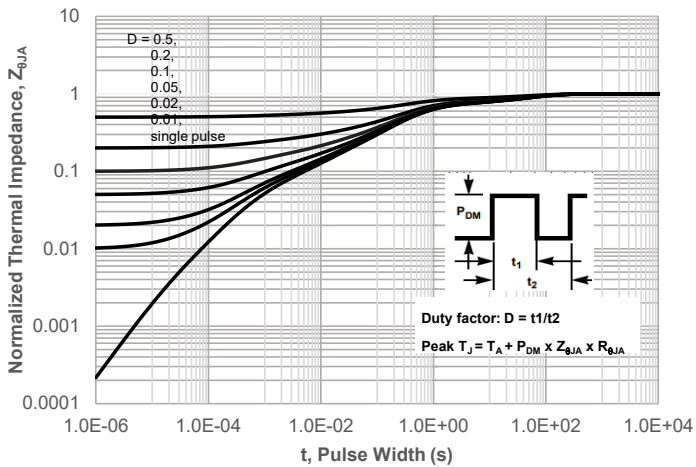
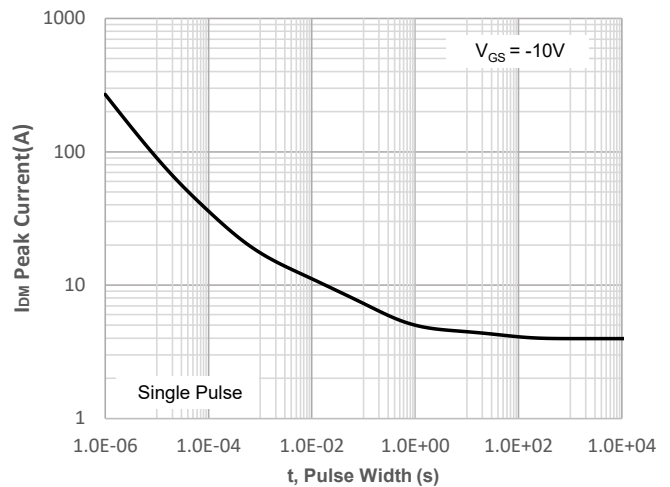


Figure 12: Peak Current Capacity



## Test Circuit

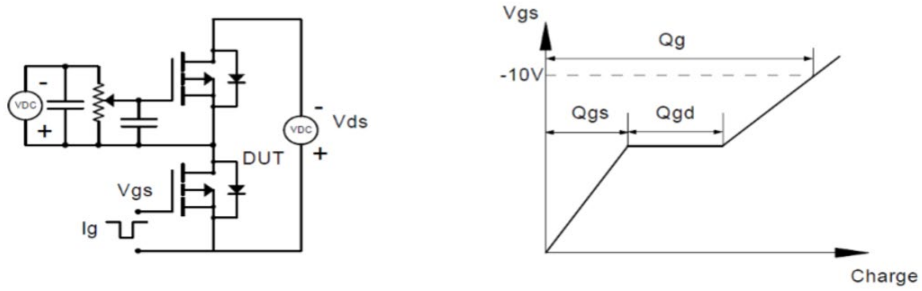


Figure 1: Gate Charge Test Circuit & Waveform

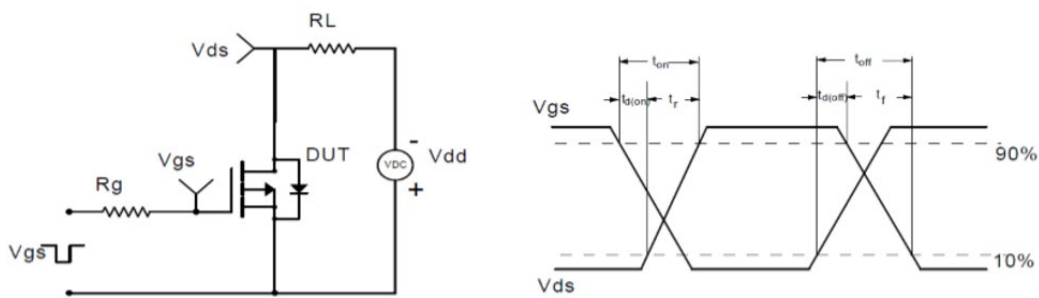


Figure 2: Resistive Switching Test Circuit & Waveform

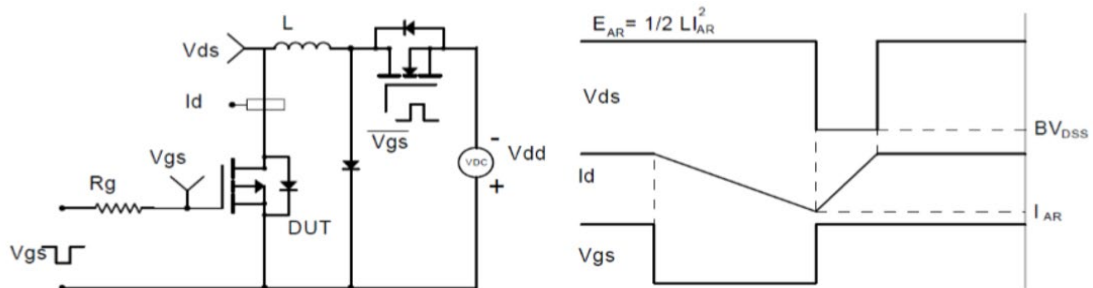


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

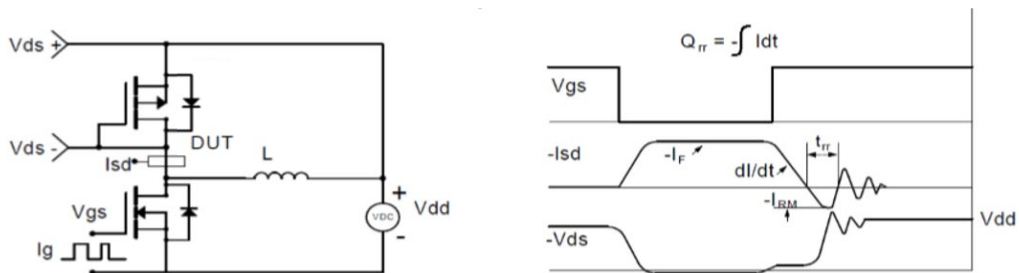
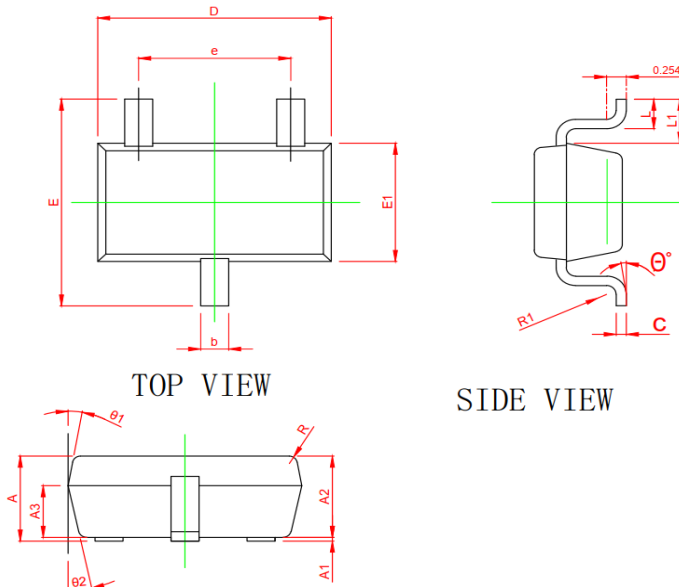


Figure 4: Diode Recovery Test Circuit & Waveform

## Package Mechanical Data(SOT-23-3L)



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	-	-	1.25
* A1	0.02	-	0.10
* A2	1.05	1.10	1.15
A3	0.65	0.70	0.75
* b	0.30	0.35	0.45
* c	0.127 BSC		
* D	2.87	2.92	2.97
* E	2.72	2.80	2.88
* E1	1.55	1.60	1.65
* e	1.85	1.90	1.95
* L	0.32	0.40	0.48
* L1	0.55	0.60	0.65
R	0.10 REF		
R1	0.12 REF		
* $\theta$	0	--	8°
$\theta1$	8°	10°	12°
$\theta2$	10°	12°	14°

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